

# isc Silicon PNP Darlington Power Transistor

2SB1560

#### DESCRIPTION

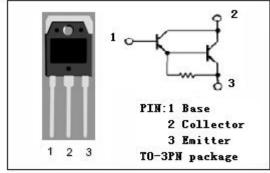
- · High DC Current Gain-
- : h<sub>FE</sub>= 5000(Min)@I<sub>C</sub>= -7A
- Low-Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= -2.5V(Max.)@I<sub>C</sub>= -7A
- · Complement to Type 2SD2390
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

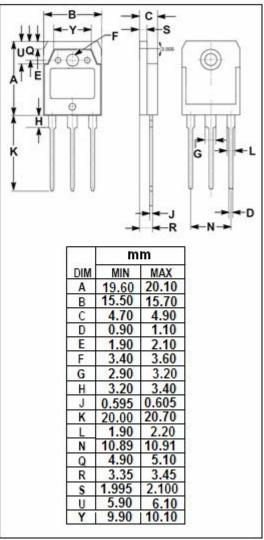


 Designed for audio, series regulator and general purpose applications.



| SYMBOL           | PARAMETER  | VALUE   | UNIT         |
|------------------|--|---------|--------------|
| V <sub>CBO</sub> | Collector-Base Voltage                               | -160    | V            |
| V <sub>CEO</sub> | Collector-Emitter Voltage                            | -150    | V            |
| V <sub>EBO</sub> | Emitter-Base Voltage                                 | -5      | V            |
| lc               | Collector Current-Continuous                         | -10     | А            |
| I <sub>B</sub>   | Base Current- Continuous                             | -1      | А            |
| Pc               | Collector Power Dissipation<br>@ T <sub>C</sub> =25℃ | 100     | W            |
| Тл               | Junction Temperature                                 | 150     | $^{\circ}$ C |
| T <sub>stg</sub> | Storage Temperature Range                            | -55~150 | $^{\circ}$ C |







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### **ELECTRICAL CHARACTERISTICS**

## $T_{\text{C}}$ =25°C unless otherwise specified

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|---|--------------------------------------|---|------|------|-------|------------|--|
| SYMBOL                                  | PARAMETER                            | CONDITIONS  | MIN  | TYP. | MAX   | UNIT       |  |
| V <sub>(BR)CEO</sub>                    | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = -30mA; I <sub>B</sub> = 0  | -150 |      |       | V          |  |
| V <sub>CE(sat)</sub>                    | Collector-Emitter Saturation Voltage | Ic= -7A; I <sub>B</sub> = -7mA  |      |      | -2.5  | V          |  |
| V <sub>BE</sub> (sat)                   | Base-Emitter Saturation Voltage      | I <sub>C</sub> = -7A; I <sub>B</sub> = -7mA   |      |      | -3.0  | V          |  |
| I <sub>CBO</sub>                        | Collector Cutoff Current             | V <sub>CB</sub> = -160V; I <sub>E</sub> = 0   |      |      | -100  | μА         |  |
| I <sub>EBO</sub>                        | Emitter Cutoff Current               | V <sub>EB</sub> = -5V; I <sub>C</sub> = 0   |      |      | -100  | μ <b>А</b> |  |
| h <sub>FE</sub>                         | DC Current Gain                      | I <sub>C</sub> = -7A; V <sub>CE</sub> = -4V   | 5000 |      | 30000 |            |  |
| Сов                                     | Collector Output Capacitance         | I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1MHz                                 |      | 230  |       | pF         |  |
| Switching Times                         |                                      |   |      |      |       |            |  |
| t <sub>on</sub>                         | Turn-on Time                         |   |      | 0.8  |       | μ <b>S</b> |  |
| t <sub>stg</sub>                        | Storage Time                         | $I_{C}$ = -7A; $I_{B1}$ = - $I_{B2}$ = -7mA, $V_{CC}$ = -70V, $R_{L}$ = 10 $\Omega$ |      | 3.0  |       | μ <b>S</b> |  |
| t <sub>f</sub>                          | Fall Time                            |   |      | 1.2  |       | μ <b>S</b> |  |

## ♦ h<sub>FE</sub> Classifications

| 0          | Р          | Y           |
|------------|------------|-------------|
| 5000-12000 | 6500-20000 | 15000-30000 |



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